查询SPB07N60S5供应商

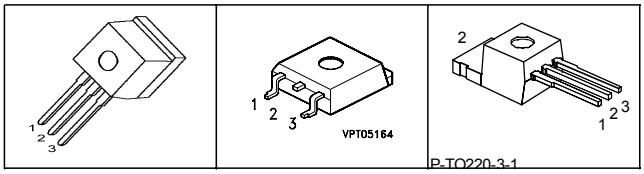
Cool MOS™ Power Transistor

V_{DS}	600	V
$R_{DS(on)}$	0.6	Ω
I_D	7.3	A

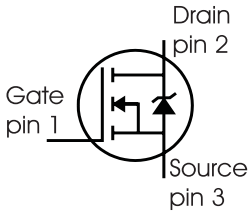
Feature

- New revolutionary high voltage technology
- Worldwide best $R_{DS(on)}$ in TO 220
- Ultra low gate charge
- Periodic avalanche rated
- Extreme d*v*/d*t* rated
- Ultra low effective capacitances
- Improved transconductance

P-TO262 P-TO263-3-2 P-TO220-3-1



Type	Package	Ordering Code	Marking
SPP07N60S5	P-TO220-3-1	Q67040-S4172	07N60S5
SPB07N60S5	P-TO263-3-2	Q67040-S4185	07N60S5
SPI07N60S5	P-TO262	Q67040-S4328	07N60S5



Maximum Ratings

Parameter	Symbol	Value	Unit
Continuous drain current T_C = 25 °C T_C = 100 °C	I_D	 7.3 4.6	A
Pulsed drain current, t_p limited by T_{jmax}	$I_{D\ puls}$	14.6	
Avalanche energy, single pulse I_D = - A, V_{DD} = 50 V	E_{AS}	230	mJ
Avalanche energy, repetitive t_{AR} limited by T_{jmax}[1] I_D = 7.3 A, V_{DD} = 50 V	E_{AR}	0.5	
Avalanche current, repetitive t_{AR} limited by T_{jmax}	I_{AR}	7.3	A
Gate source voltage	V_{GS}	±20	V
Gate source voltage AC (f >1Hz)	V_{GS}	±30	
Power dissipation, T_C = 25°C	P_{tot}	83	W
Operating and storage temperature	T_j, T_{stg}	-55... +150	°C

Maximum Ratings

Parameter	Symbol	Value	Unit
Drain Source voltage slope V_{DS} = 480 V, I_D = 7.3 A, T_j = 125 °C	dv/dt	20	V/ns

Thermal Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Thermal resistance, junction - case	R_{thJC}	-	-	1.5	K/W
Thermal resistance, junction - ambient, leaded	R_{thJA}	-	-	62	
SMD version, device on PCB: @ min. footprint @ 6 cm^2 cooling area [2)]	R_{thJA}	 - -	 - 35	 62 -	
Soldering temperature, 1.6 mm (0.063 in.) from case for 10s	T_{sold}	-	-	260	°C

Electrical Characteristics, at Tj=25°C unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D=0.25mA	600	-	-	V
Drain-Source avalanche breakdown voltage	$V_{(BR)DS}$	V_{GS}=0V, I_D=7.3A	-	700	-	
Gate threshold voltage	$V_{GS(th)}$	I_D=350µA, V_{GS}=V_{DS}	3.5	4.5	5.5	
Zero gate voltage drain current	I_{DSS}	V_{DS}=600V, V_{GS}=0V, T_j=25°C, T_j=150°C	 - -	 0.5 -	 1 100	µA
Gate-source leakage current	I_{GSS}	V_{GS}=20V, V_{DS}=0V	-	-	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	V_{GS}=10V, I_D=4.6A, T_j=25°C T_j=150°C	 - -	 0.54 1.46	 0.6 -	Ω
Gate input resistance	R_G	f=1MHz, open Drain	-	19	-	

Electrical Characteristics , at T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Characteristics						
Transconductance	g_{fs}	$V_{DS}\geq 2*I_D*R_{DS(on)max}$, I_D=4.6A	-	4	-	S
Input capacitance	C_{iss}	V_{GS}=0V, V_{DS}=25V, f=1MHz	-	970	-	pF
Output capacitance	C_{oss}		-	370	-	
Reverse transfer capacitance	C_{rss}		-	10	-	
Effective output capacitance,[3] energy related	$C_{o(er)}$	V_{GS}=0V, V_{DS}=0V to 480V	-	30	-	pF
Effective output capacitance,[4] time related	$C_{o(tr)}$		-	55	-	
Turn-on delay time	$t_{d(on)}$	V_{DD}=350V, V_{GS}=0/10V, I_D=7.3A, R_G=12Ω	-	120	-	ns
Rise time	t_r		-	40	-	
Turn-off delay time	$t_{d(off)}$		-	170	255	
Fall time	t_f		-	20	30	

Gate Charge Characteristics

Gate to source charge	Q_{gs}	V_{DD}=350V, I_D=7.3A	-	7.5	-	nC
Gate to drain charge	Q_{gd}		-	16.5	-	
Gate charge total	Q_g	V_{DD}=350V, I_D=7.3A, V_{GS}=0 to 10V	-	27	35	
Gate plateau voltage	$V_{(plateau)}$	V_{DD}=350V, I_D=7.3A	-	8	-	V

[1] Repetitve avalanche causes additional power losses that can be calculated as $P_{AV}=E_{AR}*f$.

[2] Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70 µm thick) copper area for drain connection. PCB is vertical without blown air.

[3] $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}.

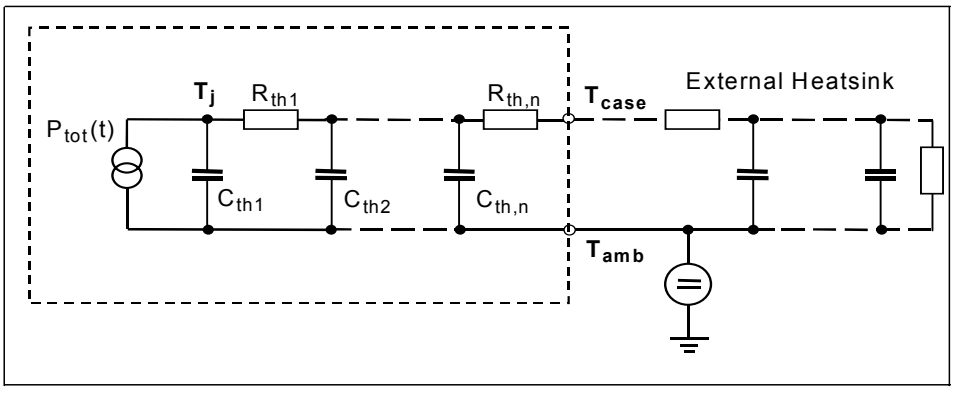
[4] $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}.

Electrical Characteristics, at T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Inverse diode continuous forward current	I_S	T_C=25°C	-	-	7.3	A
Inverse diode direct current, pulsed	I_{SM}		-	-	14.6	
Inverse diode forward voltage	V_{SD}	V_{GS}=0V, I_F=I_S	-	1	1.2	V
Reverse recovery time	t_{rr}	V_R=350V, I_F=I_S ,	-	750	1275	ns
Reverse recovery charge	Q_{rr}	di_F/dt=100A/µs	-	4.9	-	µC

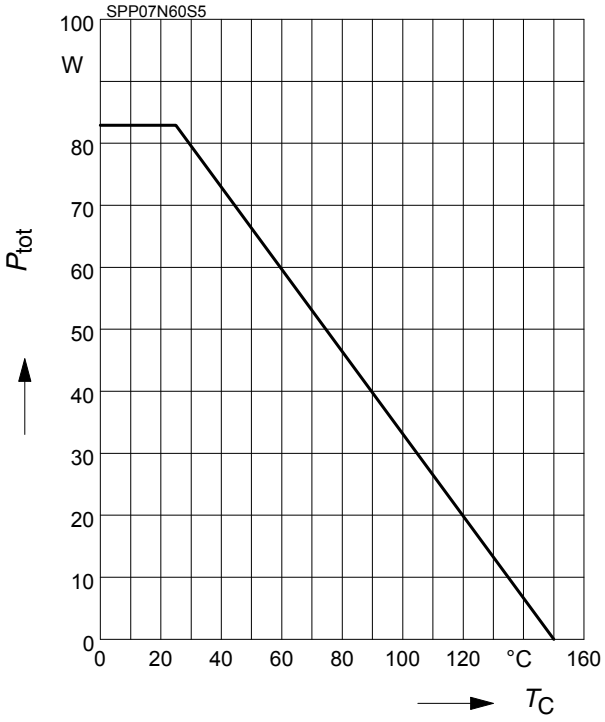
Typical Transient Thermal Characteristics

Symbol	Value	Unit	Symbol	Value	Unit
	typ.			typ.	
Thermal resistance			Thermal capacitance		
R_{th1}	0.024	K/W	C_{th1}	0.00012	Ws/K
R_{th2}	0.046		C_{th2}	0.0004578	
R_{th3}	0.085		C_{th3}	0.000645	
R_{th4}	0.308		C_{th4}	0.001867	
R_{th5}	0.317		C_{th5}	0.004795	
R_{th6}	0.112		C_{th6}	0.045	



1 Power dissipation

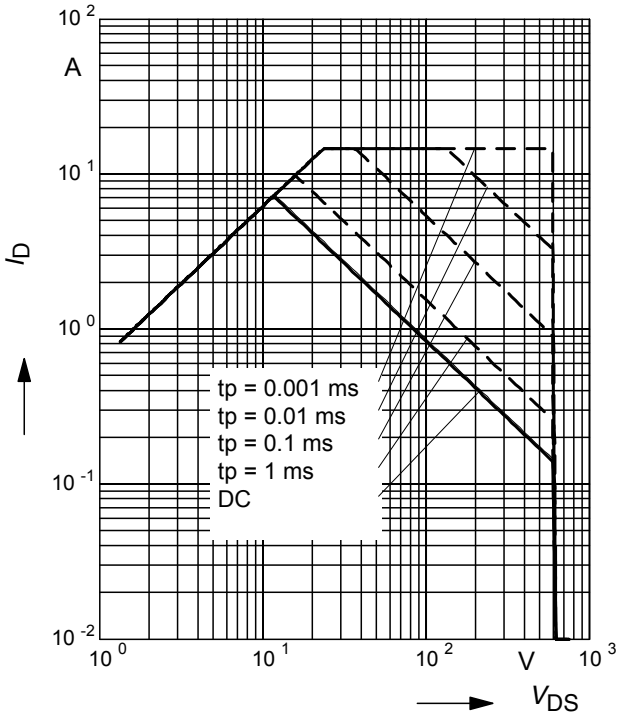
$P_{tot} = f(T_C)$



2 Safe operating area

$I_D = f(V_{DS})$

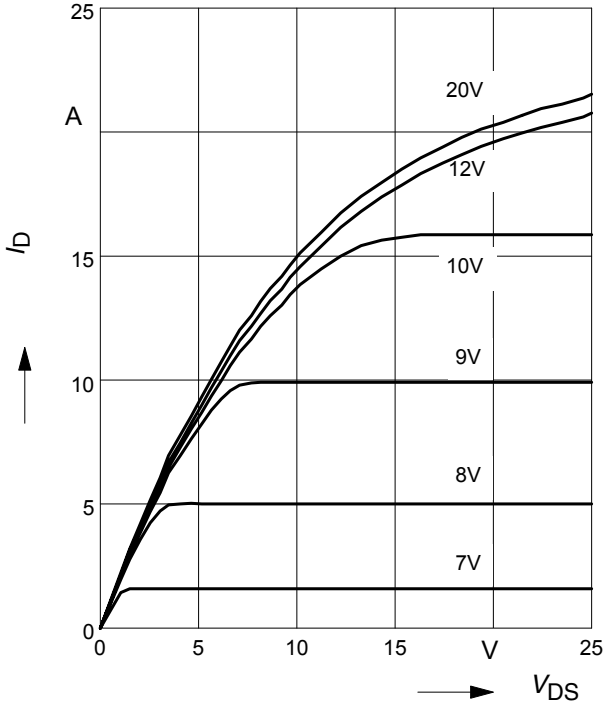
parameter : $D = 0$, T_C=25°C



3 Typ. output characteristic

$I_D = f(V_{DS})$; T_j=25°C

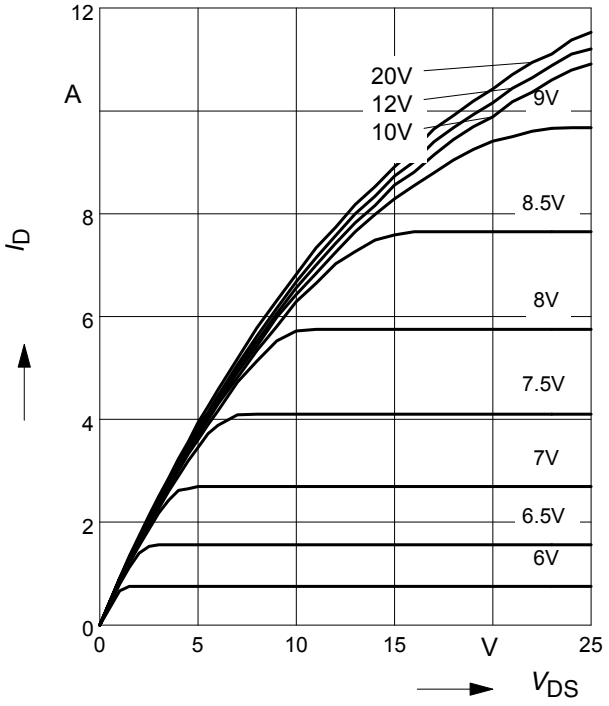
parameter: t_p = 10 µs, V_{GS}



4 Typ. output characteristic

$I_D = f(V_{DS})$; T_j=150°C

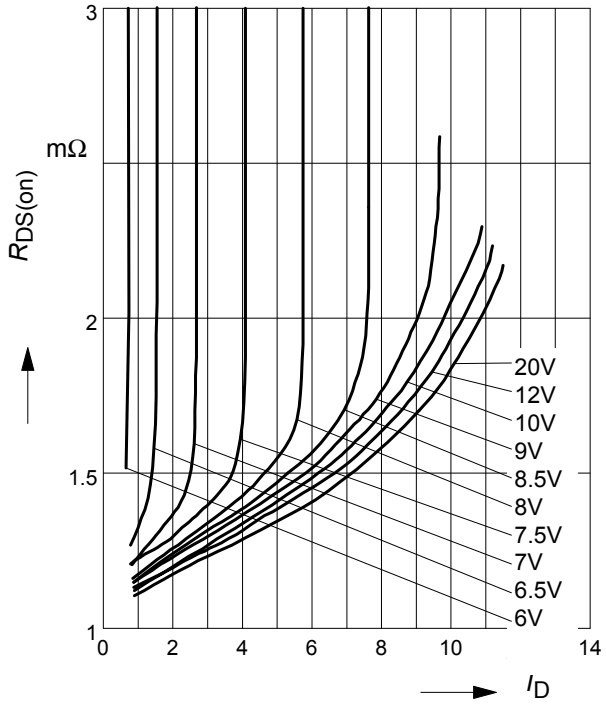
parameter: t_p = 10 µs, V_{GS}



5 Typ. drain-source on resistance

$R_{DS(on)}=f(I_D)$

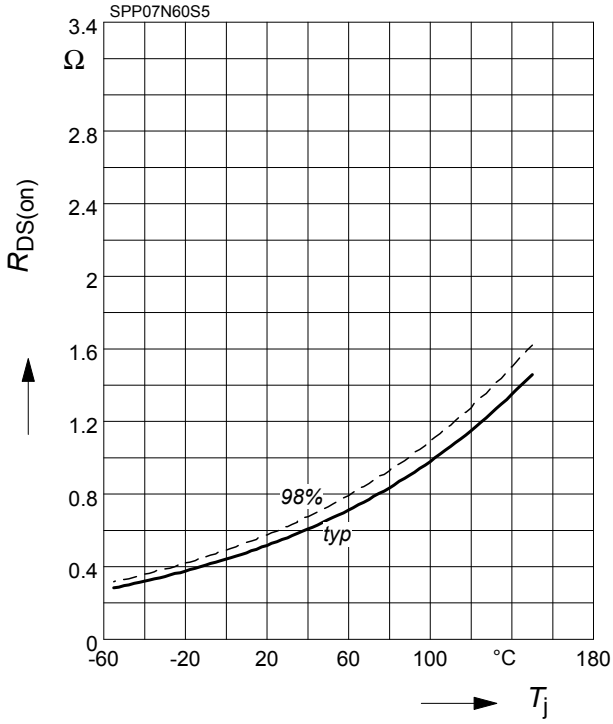
parameter: T_j=150°C, V_{GS}



6 Drain-source on-state resistance

$R_{DS(on)} = f(T_j)$

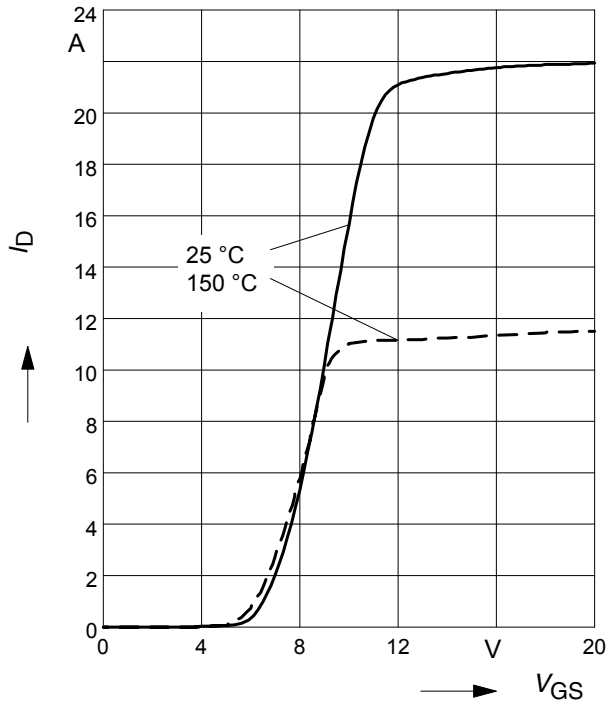
parameter : I_D = 4.6 A, V_{GS} = 10 V



7 Typ. transfer characteristics

$I_D= f(V_{GS})$; $V_{DS}\geq 2 \times I_D \times R_{DS(on)max}$

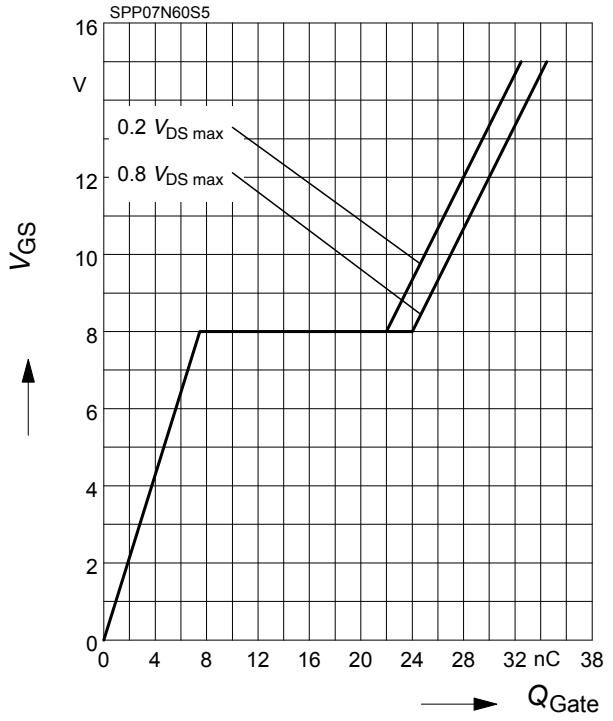
parameter: t_p = 10 µs



8 Typ. gate charge

$V_{GS} = f\ (Q_{Gate})$

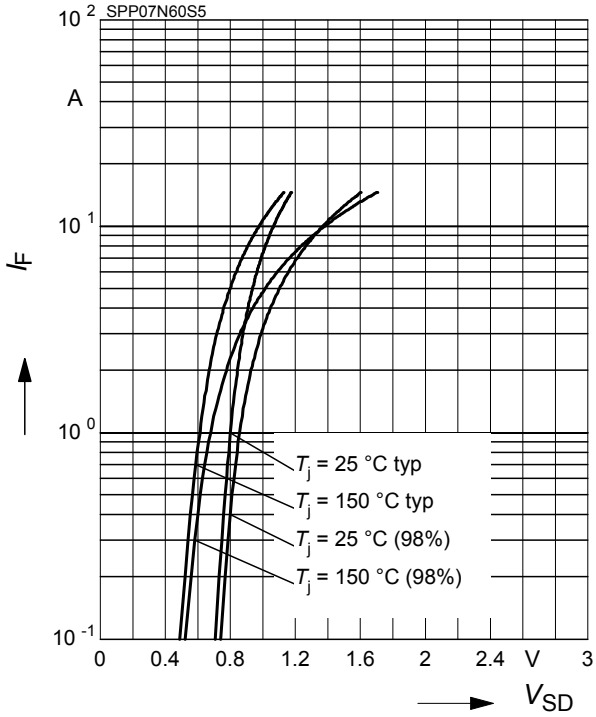
parameter: I_D = 7.3 A pulsed



9 Forward characteristics of body diode

$I_F = f(V_{SD})$

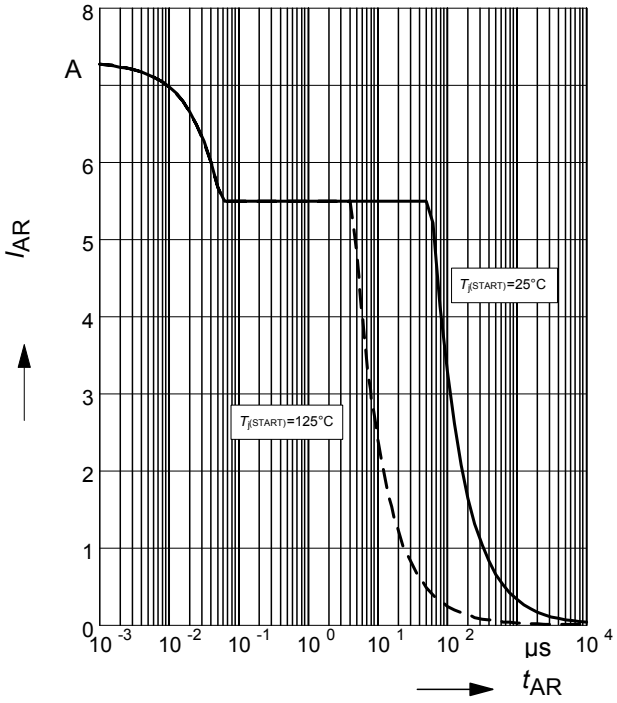
parameter: T_j , tp = 10 µs



10 Avalanche SOA

$I_{AR} = f(t_{AR})$

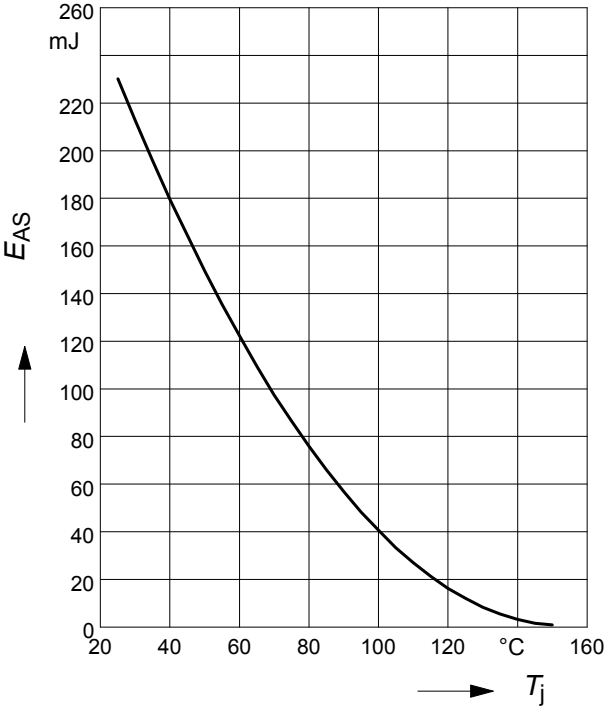
par.: $T_j \leq 150$ °C



11 Avalanche energy

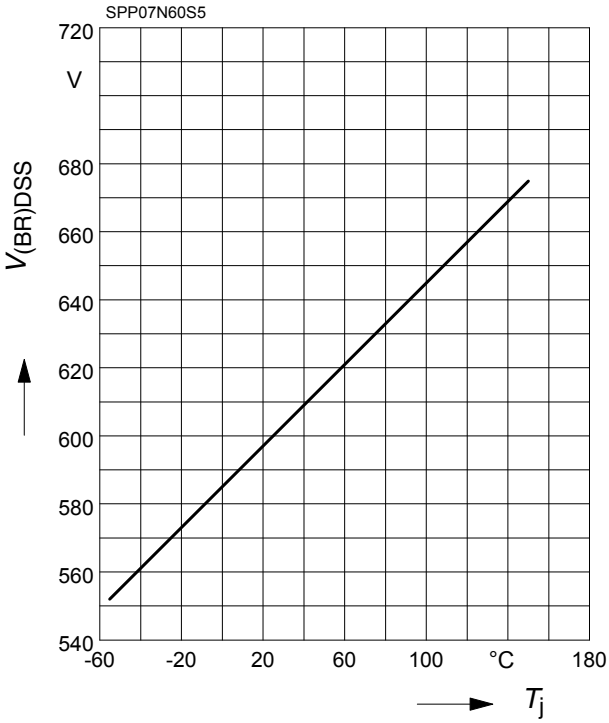
$E_{AS} = f(T_j)$

par.: I_D = - A, V_{DD} = 50 V



12 Drain-source breakdown voltage

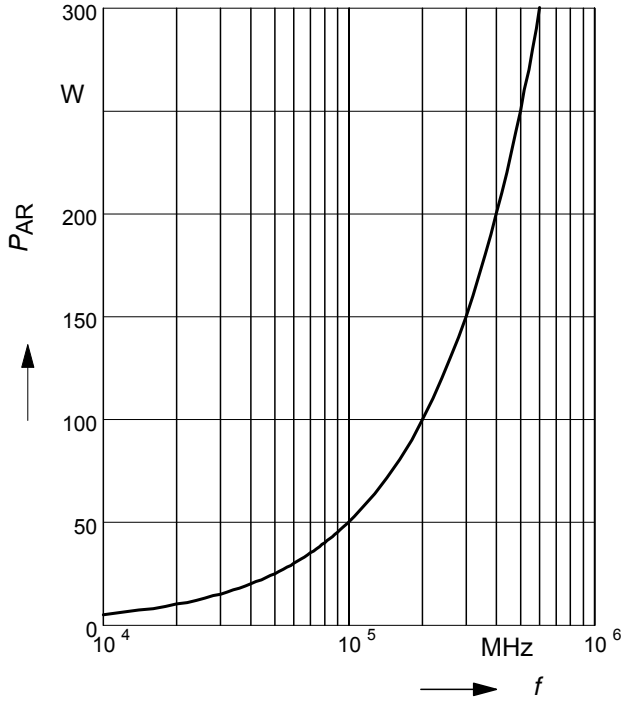
$V_{(BR)DSS} = f(T_j)$



13 Avalanche power losses

$P_{AR} = f(f)$

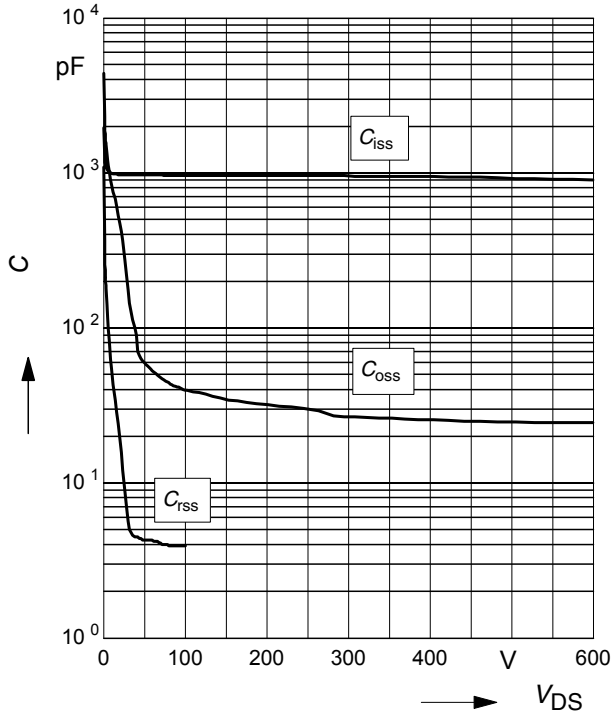
parameter: E_{AR}=0.5mJ



14 Typ. capacitances

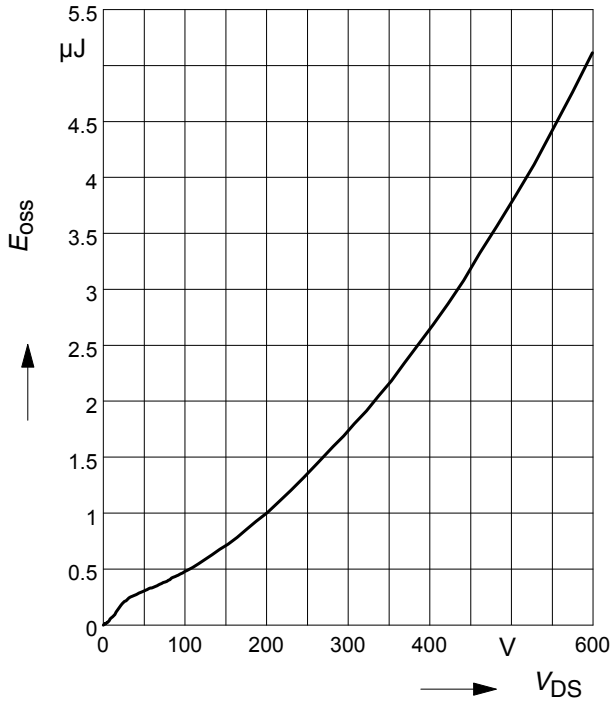
$C = f(V_{DS})$

parameter: V_{GS}=0V, f=1 MHz



15 Typ. C_{oss} stored energy

$E_{oss}=f(V_{DS})$

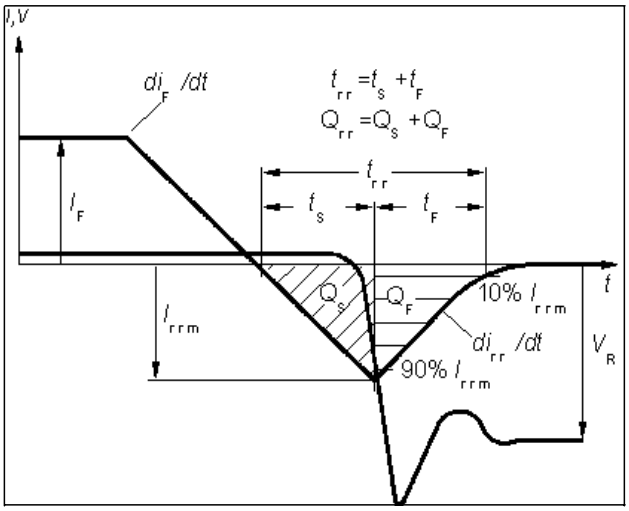


16 Typ. gate threshold voltage

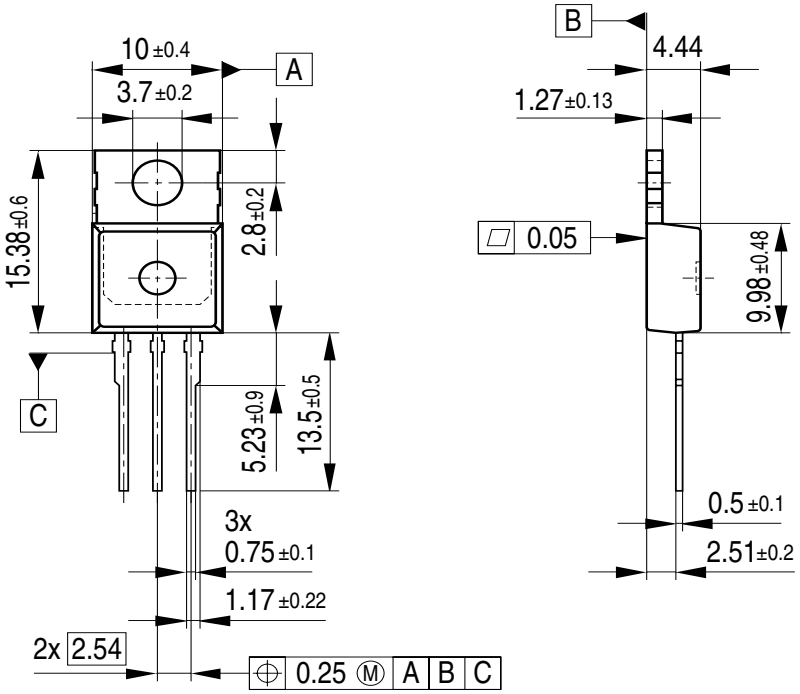
$V_{GS(th)} = f(T_j)$

parameter: $V_{GS} = V_{DS}$

Definition of diodes switching characteristics

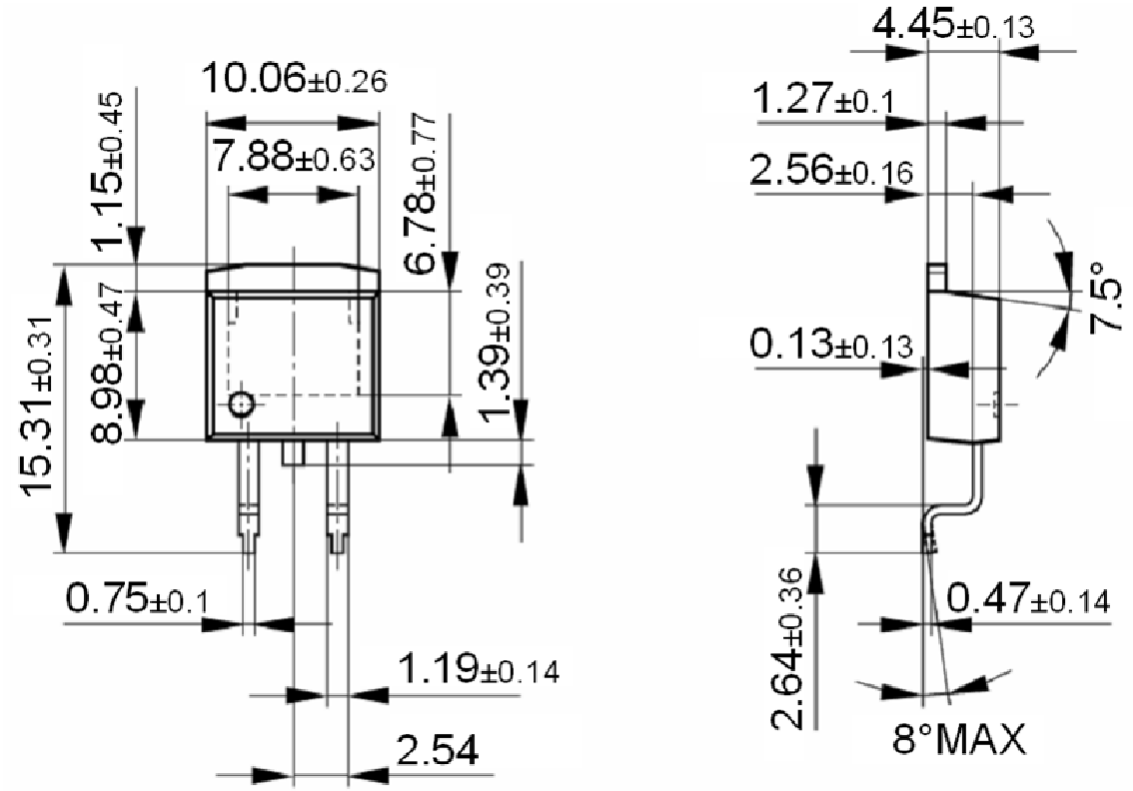


P-TO-220-3-1

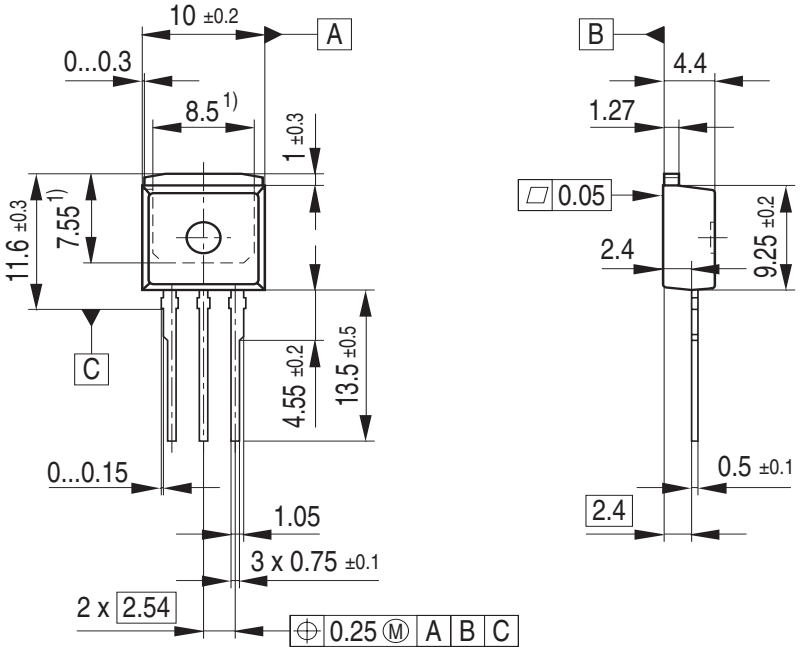


All metal surfaces tin plated, except area of cut.
Metal surface min. x=7.25, y=12.3

P-TO-263-3-2 (D^2-PAK)



P-TO-262-3-1 (I^2-PAK)



1) Typical
Metal surface min. X = 7.25, Y = 6.9
All metal surfaces tin plated, except area of cut.

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